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SOT-23 .> / / x N 3 « | • 'ož

4-CHANNEL MOSFET in a SOT-23 Plastic Package.

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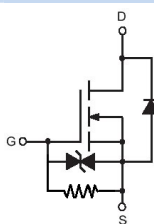
High Power and Current Handling Capability, Integrated Gate-Source Resistance, ESD Rating HBM Ú 4KV, HF Product.

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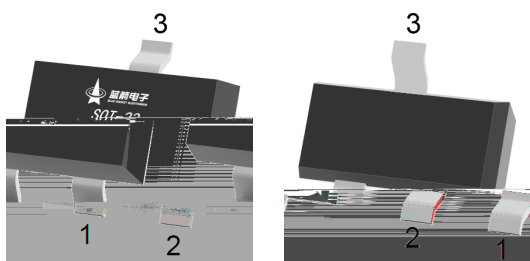
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PWM application, Load switch, Power Management

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PIN1 y G

PIN 2 y S

PIN 3 y D

, M V / 5

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See Marking Instructions.

Figure 25 :)

@ f Parameter		... Z Symbol	f > Rating	% y Unit
Drain–Source Voltage		V _{DS}	80	V
Drain Current		I _D	2.2	A
Drain Current - Pulsed		I _{DM}	9	A
Gate-Source Voltage		V _{GS}	±20	V
Power Dissipation		P _D	2	W
Operating and Storage Temperature Range		T _J , T _{STG}	-55 150	
Maximum Junction-to-Ambient	t 0 10s	R _{θJA}	62.5	/W
Maximum Junction-to-Ambient	Steady-State		102	/W
Maximum Junction-to-Lead	Steady-State	R _{θJL}	55	/W

Figure 25 :)

@ f Parameter	... Z Symbol	y i Ú ^ Test Conditions	Â 4 > Min	Á ° > Typ	Â Ý > Max	% y Unit
Drain–Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250 A	80	90		V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} I _D =250 A	2	3	4	V
Static Drain–Source On–Resistance	R _{DS(on)}	V _{GS} =10V I _D =1A		188	250	m
		V _{GS} =6V I _D =1A		280	350	m
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =60V V _{GS} =0V			-1.0	A
Gate-Body leakage current	I _{GSS}	V _{GS} =±20V V _{DS} =0V			±500	A
Drain-Source Diode Forward Voltage	V _{SD}	V _{GS} =0V I _S =1A			1.2	V
Gate resistance	R _g	f=1MHz		3.7		
Gate- Source Resistance	R _{GS}			50		K
Input Capacitance	C _{iss}	V _{DS} =25V V _{GS} =0V f=1.0MHz		72		pF
Output Capacitance	C _{oss}			34		
Reverse Transfer Capacitance	C _{rss}			12		
Total Gate Charge	Q _g	V _{DS} =40V V _{GS} =10V I _D =1.5A		2.2		nC
Gate-to-Source Charge	Q _{gs}			0.56		
Gate-to-Drain Charge	Q _{gd}			0.42		
Turn–On Delay Time	t _{d(on)}	V _{DS} =40V V _{GS} =10V I _D =1.5A R _{GEN} =2		7.8		ns
Turn–On Rise Time	t _r			1.5		
Turn–Off Delay Time	t _{d(off)}			11		
Turn–Off Fall Time	t _f			6.7		

Electrical Characteristics

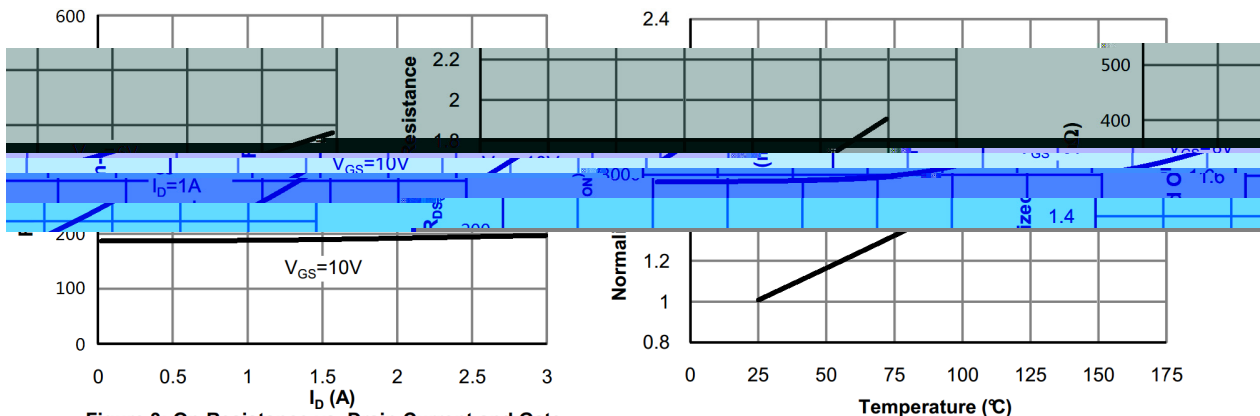
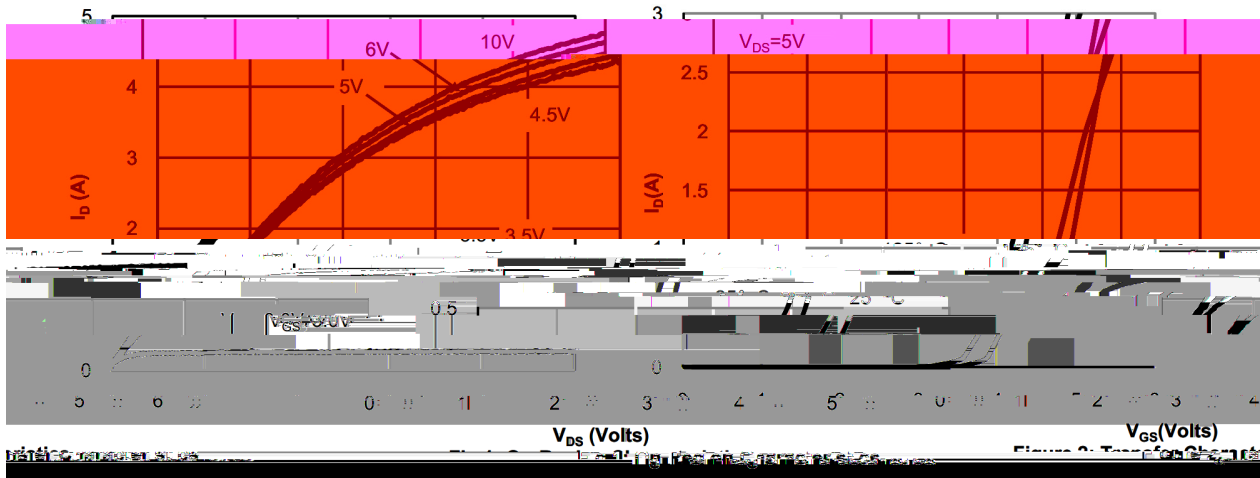
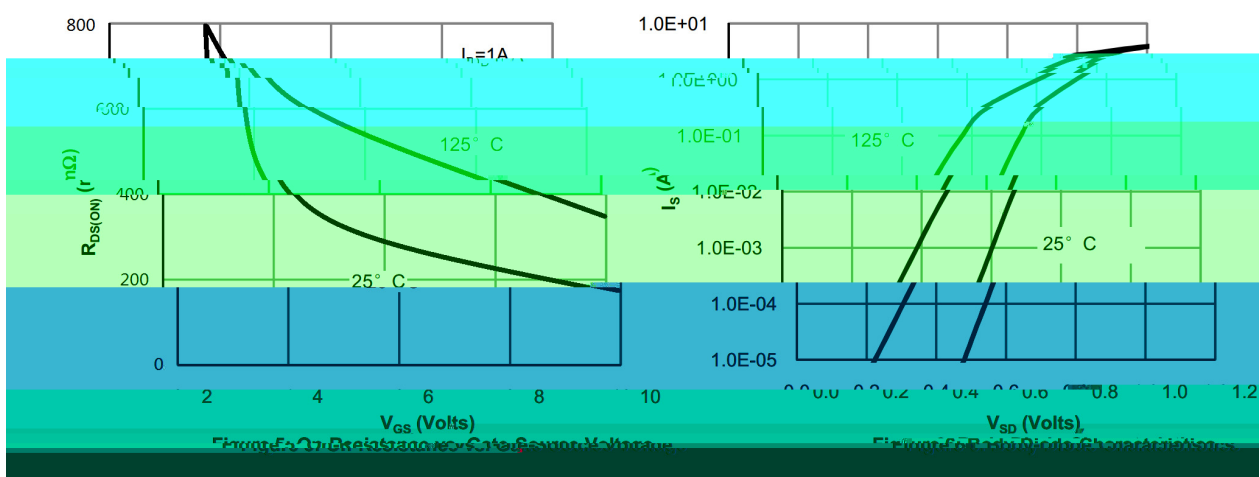


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

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Figure 4: On-Resistance vs. Junction Temperature



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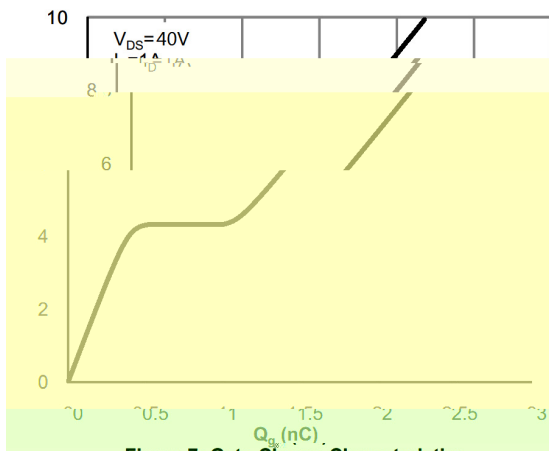


Figure 7: Gate Charge Characteristics

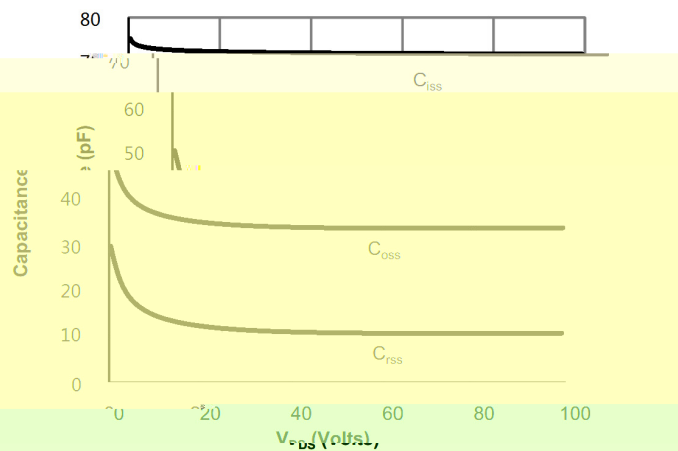


Figure 8: Capacitance Characteristics

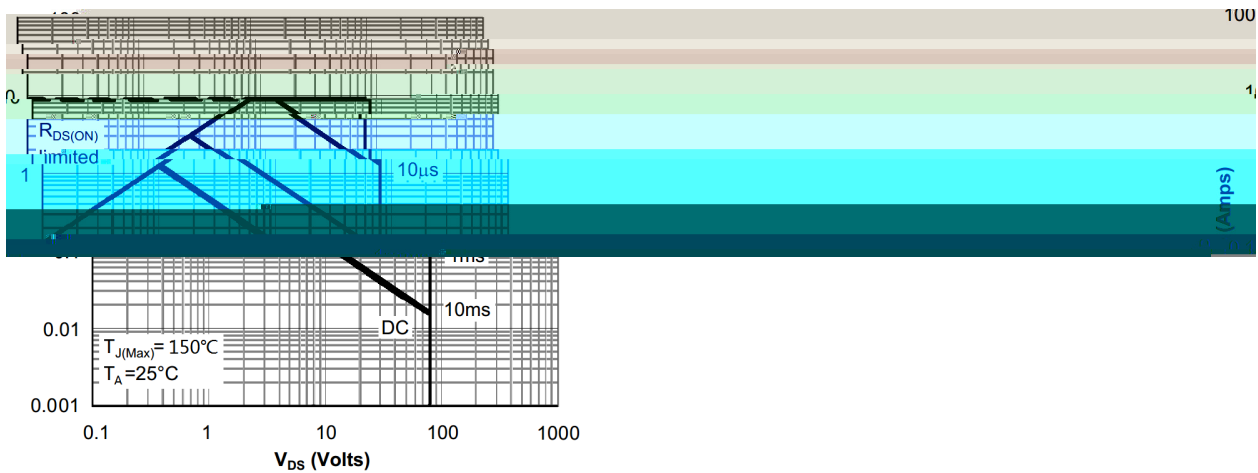


Figure 9: Maximum Forward Biased Safe Operating Area

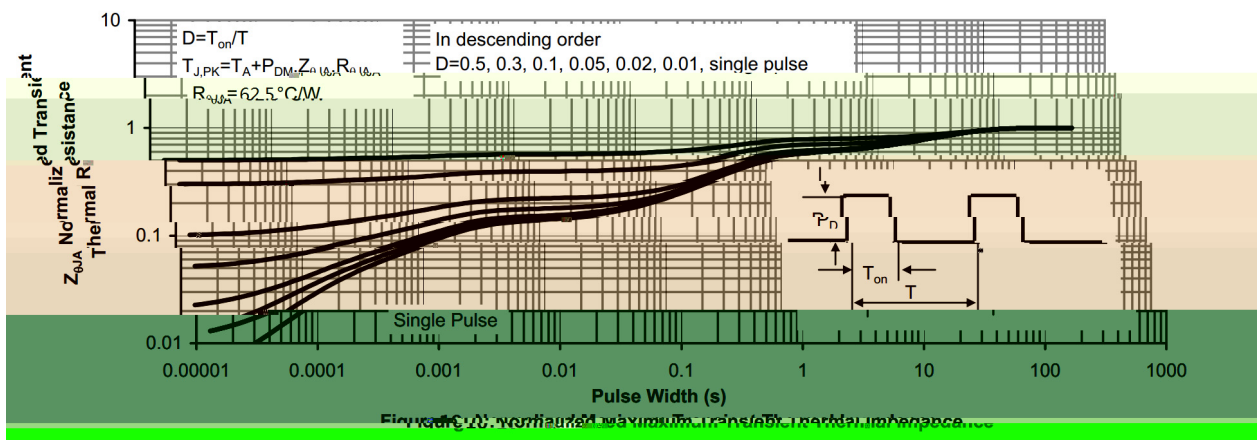
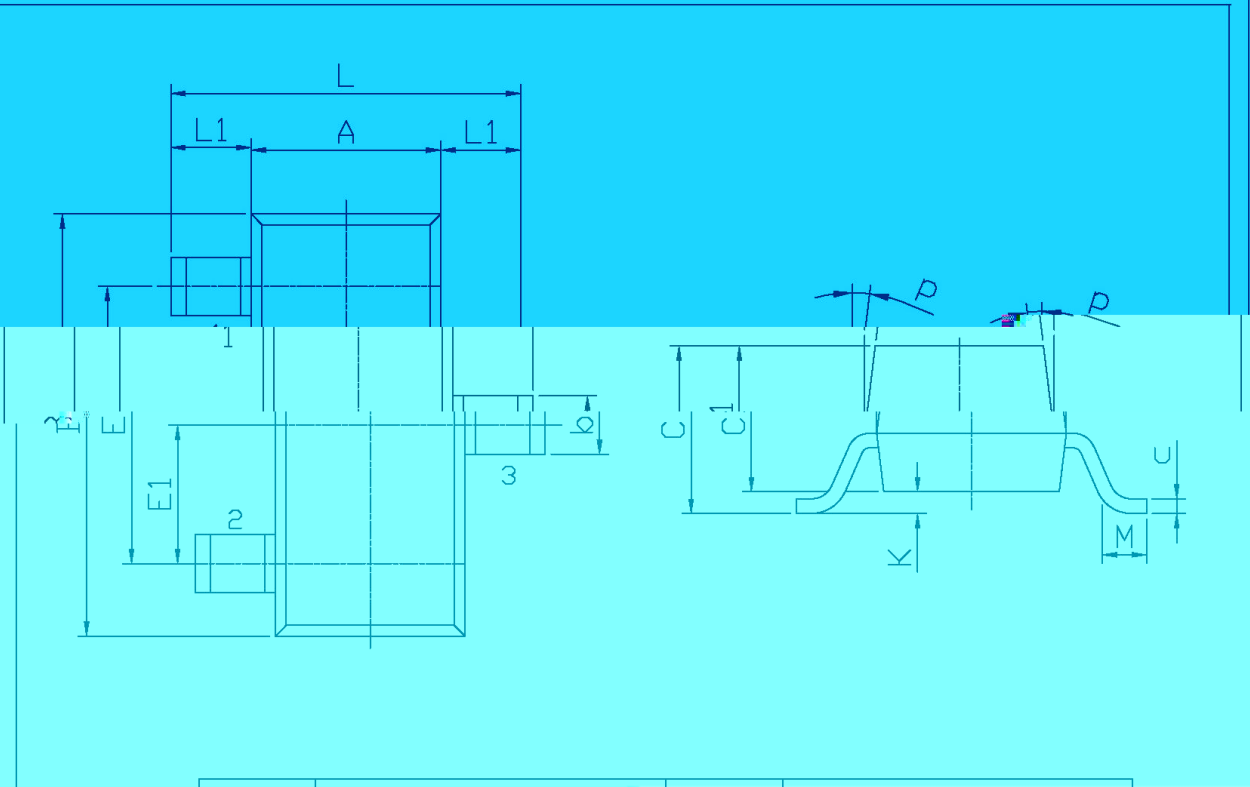


Figure 10: Normalized Maximum Transient Thermal Impedance

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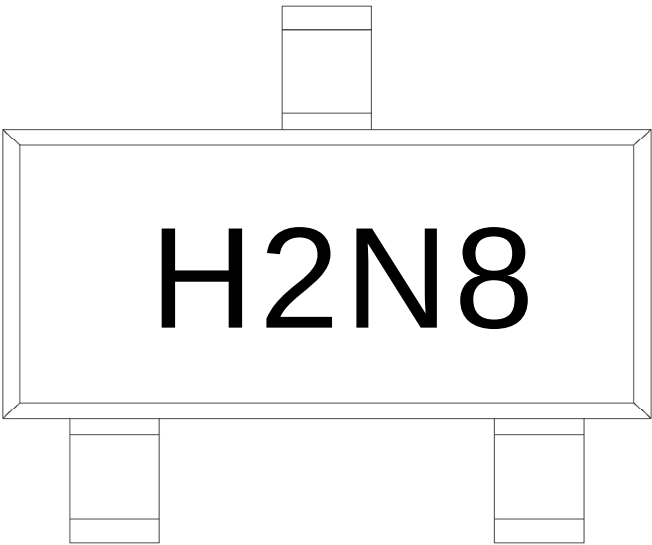
SOT-23

单位: mm



Symbol	Dimensions In Millimeters		Symbol	Dimensions In Millimeters	
	Min	Max		Min	Max
L	2.2	2.7	C	1.30Max	
L1	0.45	0.65	C1	0.90	1.20
A	1.15	1.50	c	0.05	0.20
R	2.70	3.40			

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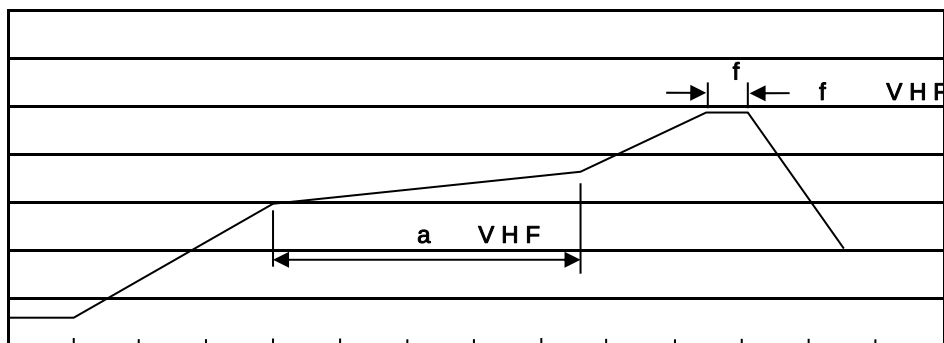
Note:

H y Company Code

2N8: Product Type

šWD t...•Žč (x/) / :KSVKXGZ[XK 6XULORK LUX /8 8KLRU] 9URJKXOTM 6

7HPSHUDWXUH



7LPH VHF

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10• Ä ½ “† 150 ½180 - k ž • 60 ½90sec;

20• Q > “† 245 r5 - k ž • 4 Ò 5 r0.5sec;

30•D N ò i Ò 0 ,† 2 ½10 - /sec.

Note:

1.Preheating:150~180 - , Time:60~90sec.

2.Peak Temp.:245 r5 - , Duration:5 r0.5sec.

3. Cooling Speed: 2~10 - /sec.

ÂD /Că p ¯ »] /

“† y 260 r5 -

ž • y 10 r1 sec.

Temp.:260 r5 -

Time:10 r1 sec

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2 & x / REEL

Package Type 7>û ~ E	Units ;>û H					Dimension ;>û p . (unit /mm³)		
	Units/Reel /-	Reels/Inner Box -- /-	Units/Inner Box /-	Inner Boxes/Outer Box - /1ç	Units/Outer Box /1ç	Reel	Inner Box	Outer Boxç
SOT-23	3,000	10	30,000	6	180,000	7 s ×8	180×120×180	390×385×205

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